

What is claimed is;

1. A fine pattern forming material comprising a water-soluble resin, a water-soluble crosslinking agent and a solvent consisting of water or a mixed solvent of water and a water-soluble organic solvent, characterized in that the above fine pattern forming material comprises an amine compound which is at least one selected from the group consisting of a primary amine compound consisting of hydrazine, urea, amino acid, a glucosamine derivative and a polyallylamine derivative, an amino group of which is partially protected at least by one selected from the group consisting of an alkyloxycarbonyl group, an aryloxycarbonyl group and an alkylcarbonyl group, and a quaternary amine compound thereof consisting of dimethylammonium salt, trimethylammonium salt, tetramethylammonium salt, dimethylethylbenzylammonium salt and N-methylpyridinium salt and that pH value of the above fine pattern forming material exceeds 7.0.

2. The fine pattern forming material according to claim 1 wherein the above water-soluble resin is at least one selected from the group consisting of a polyvinylalcohol derivative, a polyvinylpyrrolidone derivative and a polyacrylic acid derivative and the above water-soluble crosslinking agent is at least one selected from the group consisting of a melamine derivative and a urea derivative.

3. The fine pattern forming material according to claim 1 or 2, wherein the above amine compound is a polyallylamine derivative having the molecular weight of 1,000 to 10,000.

4. The fine pattern forming material according to any one of claims 1 to 3 further comprising a surfactant.

5. The fine pattern forming material according to claim 4, wherein the above surfactant is at least one selected from the group consisting of an anionic surfactant consisting of alkylsulfonate, alkylbenzene sulfonic acid and alkylbenzenesulfonate, a cationic surfactant consisting of laurylpyridinium chloride and laurylmethylammonium chloride and a nonionic surfactant consisting of polyoxyethylene octylether, polyoxyethylene laurylether and polyoxyethylene acetylenic glycolether.

6. A fine pattern forming method which is characterized in comprising a step of forming a resist pattern made of a photoresist on a substrate, a step wherein a coating layer is formed by applying the fine pattern forming material described in any one of claims 1 to 5, a step wherein the area neighboring to a resist pattern is crosslinked and/or cured by heating the before-described resist pattern and the before-described coated layer and by a diffusion of an acid from the resist pattern and a step wherein the before-described coated layer is developed by water after heating.